

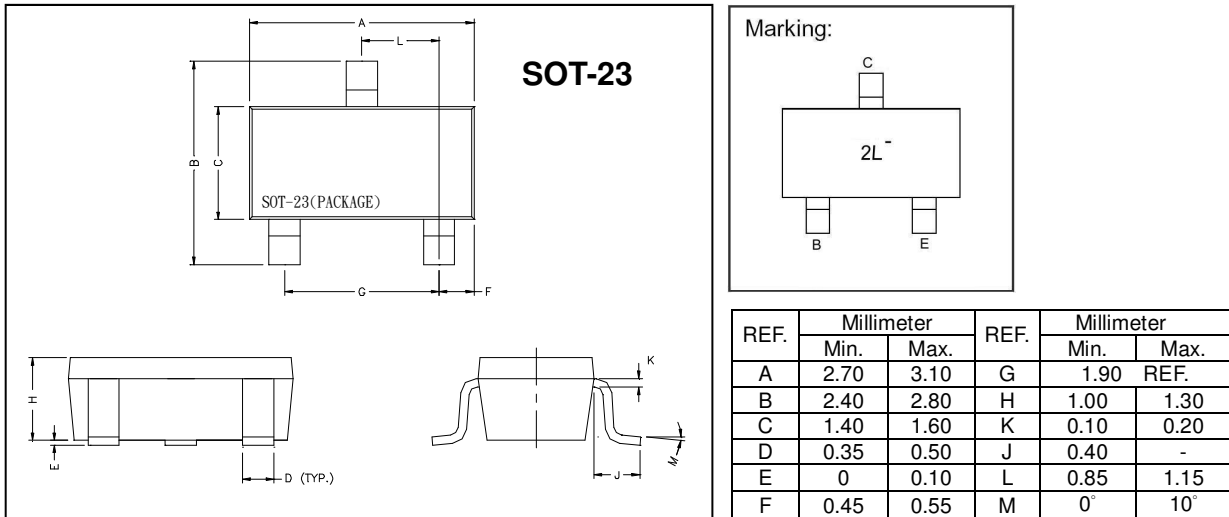
GMBT5401

PNP EPITAXIAL PLANAR TRANSISTOR

Description

The GMBT5401 is designer for general purpose applications requiring high breakdown voltages.

Package Dimensions



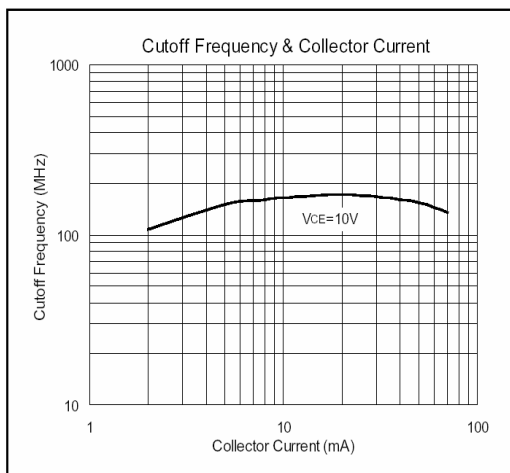
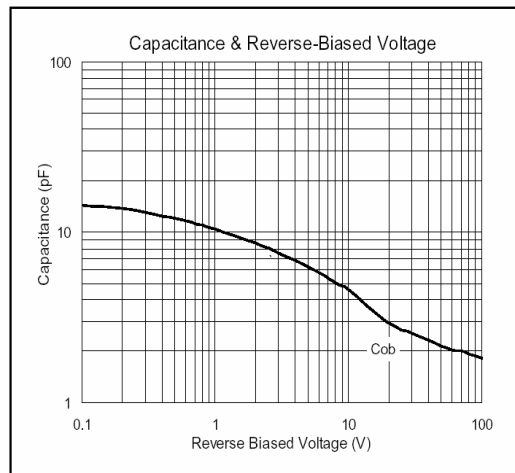
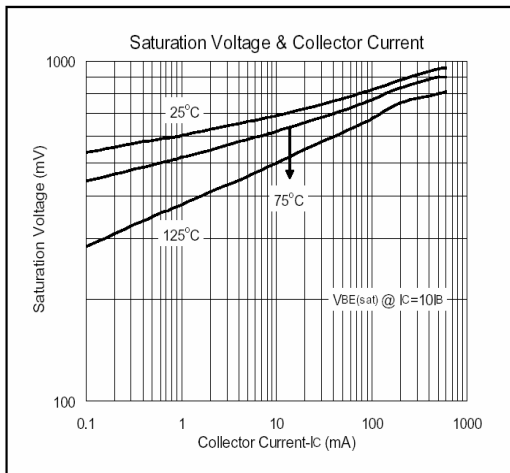
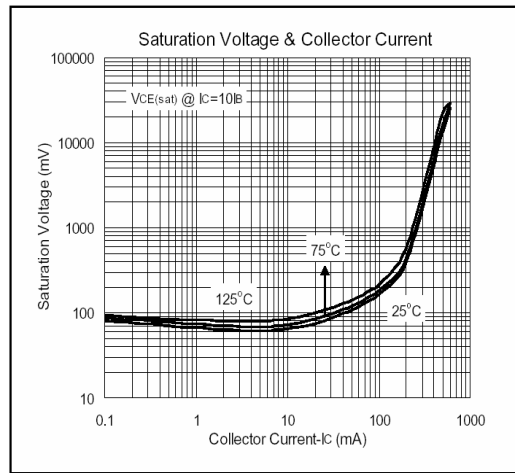
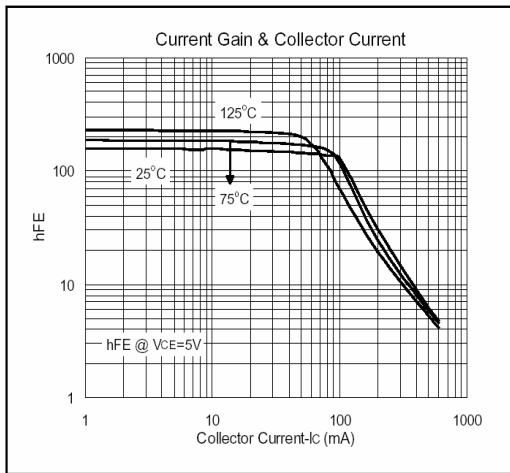
Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55 ~ +150	°C
Collector to Base Voltage	VCBO	-160	V
Collector to Emitter Voltage	VCEO	-150	V
Emitter to Base Voltage	VEBO	-5	V
Collector Current	IC	-600	mA
Total Power Dissipation	PD	225	mW

Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-160	-	-	V	IC=-100uA, IE=0
BVCEO	-150	-	-	V	IC=-1mA, IB=0
BVEBO	-5	-	-	V	IE=-10uA, IC=0
ICBO	-	-	-50	nA	VCB=-120V, IE=0
VCE(sat)1	-	-	-200	mV	IC=-10mA, IB= -1mA
VCE(sat)2	-	-	-500	mV	IC=-50mA, IB= -5mA
VBE(sat)1	-	-	-1	V	IC=-10mA, IB= -1mA
VBE(sat)2	-	-	-1	V	IC=-50mA, IB= -5mA
hFE1	50	-	-		VCE=-5V, IC= -1mA
hFE2	60	-	240		VCE=-5V, IC= -10mA
hFE3	50	-	-		VCE=-5V, IC= -50mA
fT	100	-	300	MHz	VCE=-10V, IC= -10mA, f=100MHz
Cob	-	-	6	pF	VCB= -10V, f=1MHz

Characteristics Curve



Important Notice:

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of GTM.
- GTM reserves the right to make changes to its products without notice.
- GTM semiconductor products are not warranted to be suitable for use in life-support Applications, or systems.
- GTM assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.

Head Office And Factory:

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
TEL : 86-21-5895-7671 FAX : 86-21-38950165